

SUB E1  
G1  
D1

32. (Twice amended) A polishing pad assembly for polishing a semiconductor wafer, said assembly comprising:  
a belt forming a closed loop; and  
at least one chemical mechanical planarization polishing pad mounted on the belt;  
wherein said belt is formed of metal.

SUB E2  
G2  
D2

34. (Twice amended) A polishing pad assembly for polishing a semiconductor wafer, said assembly comprising:  
a first roller;  
at least one additional roller;  
a belt forming a closed loop, which belt is mounted on said first roller and said at least one additional roller;  
at least one chemical mechanical planarization polishing pad mounted to said belt;  
and  
a drive system coupled to at least said first roller to rotate said first roller and to cause said belt and said chemical mechanical planarization polishing pad to move in a path;  
wherein said belt is formed of metal.

SUB E3  
G3  
D3

36. (Amended) A polishing pad assembly for polishing a semiconductor wafer, said assembly comprising:  
a belt forming a closed loop; and  
at least one chemical mechanical planarization polishing pad mounted on the belt;  
wherein said belt comprises a polyurethane material.

SUBP3

3

37. (Amended) A polishing pad assembly for polishing a semiconductor wafer, said assembly comprising:

a first roller;

at least one additional roller;

a belt forming a closed loop, which belt is mounted on said first roller and said at least one additional roller;

at least one chemical mechanical planarization polishing pad mounted to said belt;

and

a drive system coupled to at least said first roller to rotate said first roller and to cause said belt and said chemical mechanical planarization polishing pad to move in a path;

wherein said belt comprises a polyurethane material.

38. (Amended) A polishing pad assembly for polishing a semiconductor wafer, said assembly comprising:

a belt forming a closed loop; and

at least one chemical mechanical planarization polishing pad mounted on the belt;

wherein said belt comprises a high-strength polymer.

40. (Amended) A polishing pad assembly for polishing a semiconductor wafer, said

assembly comprising:

a first roller;

at least one additional roller;

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